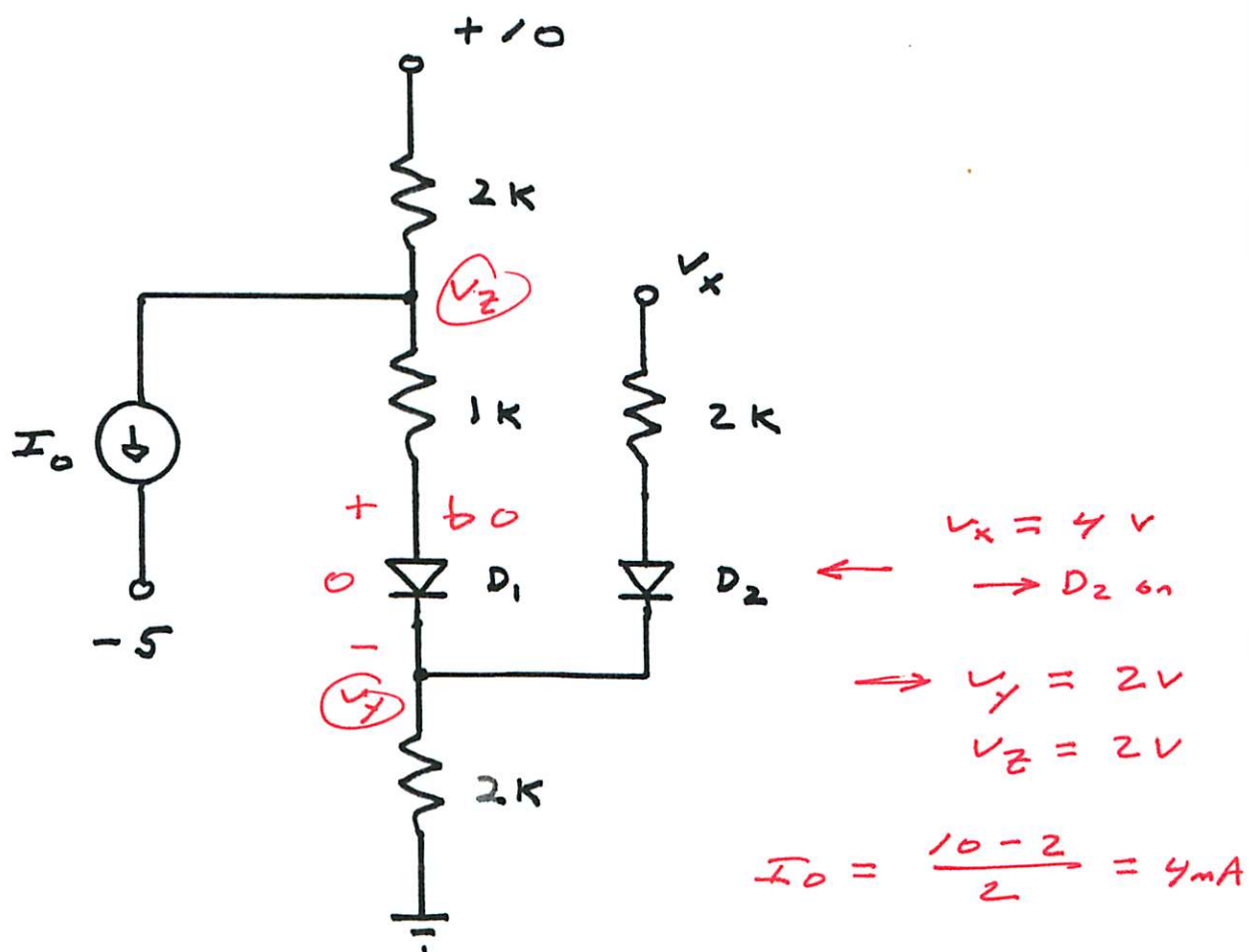


Problem 1

A. Determine the value for I_o that puts D_1 at breakpoint if $v_x = +4$ V.

B. Determine the value for I_o that puts D_1 at breakpoint if $v_x = -4$ V.



$$v_x = -4$$
 V $\rightarrow D_2$ off $V_y = V_z = 0$

$$I_o = \frac{10 - 0}{2} = 5$$
 mA

$$115 \text{ V rms}$$

$$\text{amplitude} = 115\sqrt{2} = 163 \text{ V}$$

$$\uparrow 60 \text{ Hz}$$

Problem 2

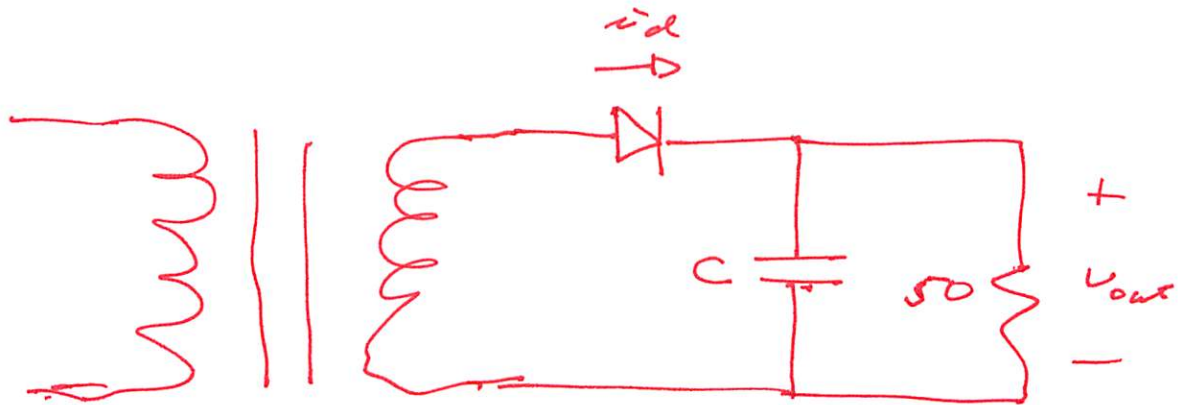
You have been asked to design a power cube that will plug into a wall outlet. The design must meet the following specifications:

- The output is 10 V dc with no more than 0.5-V ripple.
- Acceptable loads will require up to 2 Watts.
- The design has to be cheap with a minimum number of discrete parts.

$$\frac{V^2}{R} = 2 \quad \frac{100}{R} = 2 \quad R = 50 \Omega$$

$\hookrightarrow \frac{1}{2}$ -wave rectifier + C

Draw the circuit inside the power cube and indicate the important component specifications.



$$N : 1$$

step down

$$\frac{V_{\text{ripple}}}{V_{\text{max}}} = \frac{T}{RC} = 0.05$$

$$N = \frac{163}{10} = 16.3$$

$$C = \frac{1}{60 \times 50 \times 0.05}$$

$$= 6.67 \text{ mF}$$

$$\cos \phi = 1 - \frac{V_{\text{ripple}}}{V_{\text{max}}} \rightarrow \phi = 18.2^\circ$$

$$i_d(\text{max}) = V_{\text{max}} C \omega \sin \phi$$

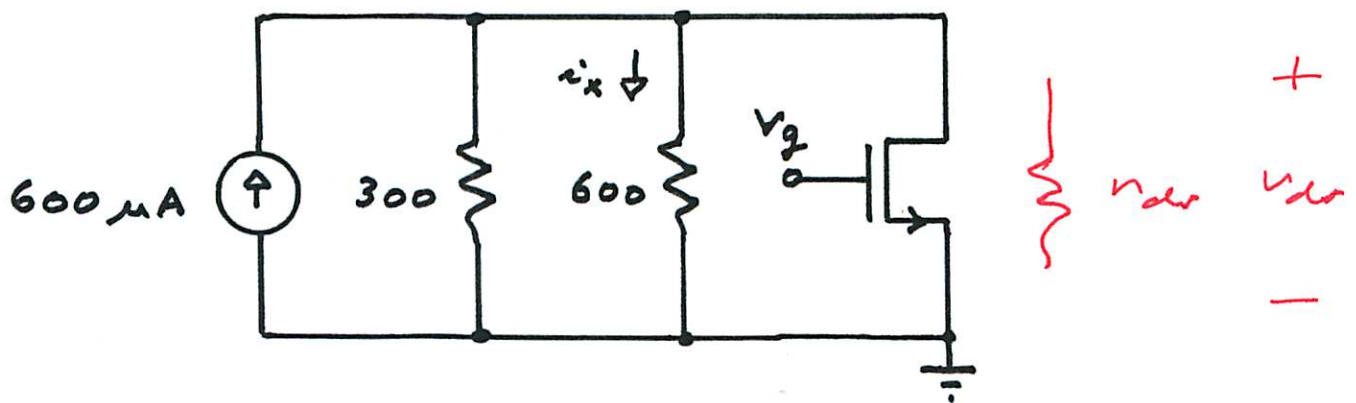
$$= 10 \times 6.67 \times 10^{-3} \times 2\pi \times 60 \times \sin \phi$$

$$= 7.85 \text{ A}$$

Problem 3

The MOSFET has $K'W/L = 2 \text{ mA/V}^2$ and $V_T = 1 \text{ V}$.

Estimate V_g such that $i_x = 100 \mu\text{A}$.



Current divider

$$100 \mu\text{A} = 600 \mu\text{A} \cdot \frac{\frac{1}{600}}{\frac{1}{300} + \frac{1}{600} + \frac{1}{r_{ds}}}$$

$$\rightarrow r_{ds} = 200 \Omega$$

$$r_{ds}^{-1} = \frac{1}{200} = \underbrace{5 \times 10^{-3}}_{\substack{1 \\ 200}} = K' \frac{W}{L} (V_{gs} - V_T) = 2 \times 10^{-3} \times (V_{gs} - 1)$$

$$\rightarrow V_{gs} - 1 = \frac{5}{2} \quad \underline{V_{gs} = 3.5 \text{ V}}$$

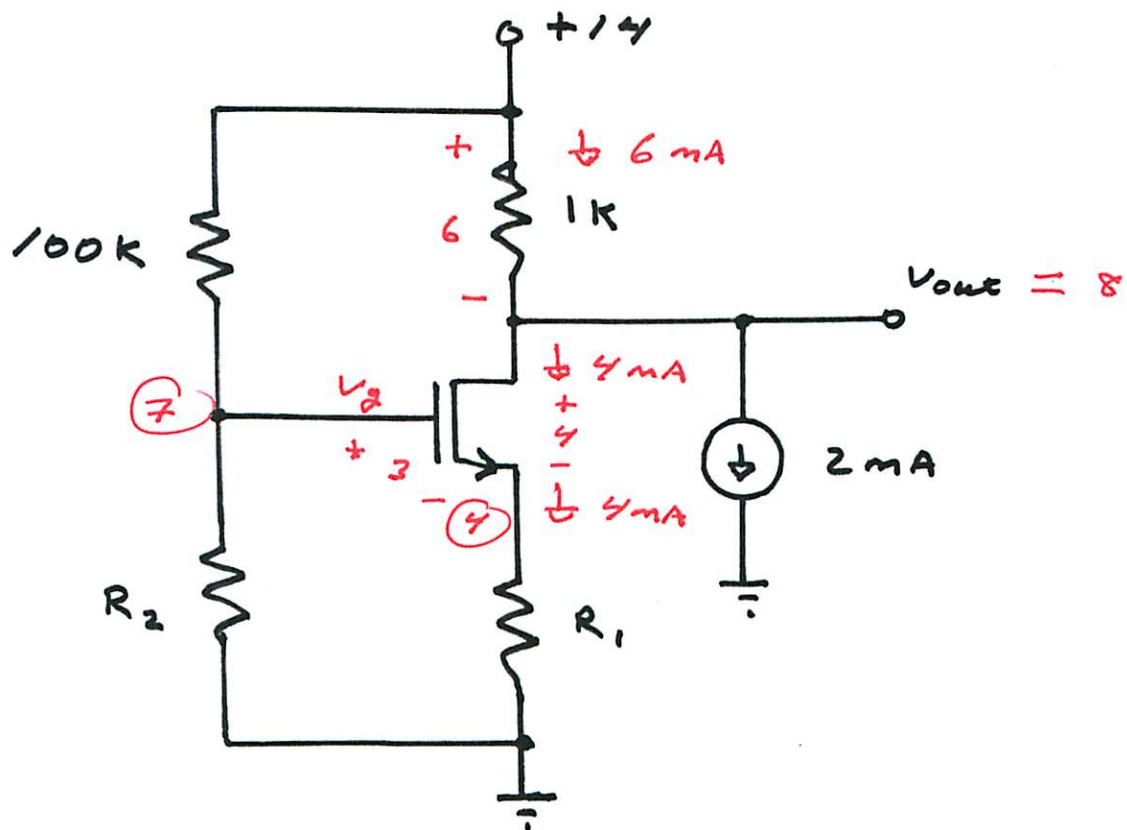
$$300 \parallel 600 \parallel r_{ds} = 100 \Omega$$

$$\rightarrow V_{ds} = 0.06 \text{ V} \rightarrow \text{negative } V$$

Problem 4

The MOSFET has $K'W/L = 2 \text{ mA/V}^2$ and $V_T = 1 \text{ V}$.

The MOSFET operates with v_{ds} 2 V higher than that needed to ensure the saturation mode, and $v_{out} = 8 \text{ V}$. Complete the design.



$$i_d = 4 = \frac{1}{2}(2)(v_{gs} - 1)^2 \rightarrow v_{gs} = 3, \text{ } \cancel{-X}$$

$$\text{saturation edge} \rightarrow v_{ds} = v_{gs} - 1 = 2 \text{ V}$$

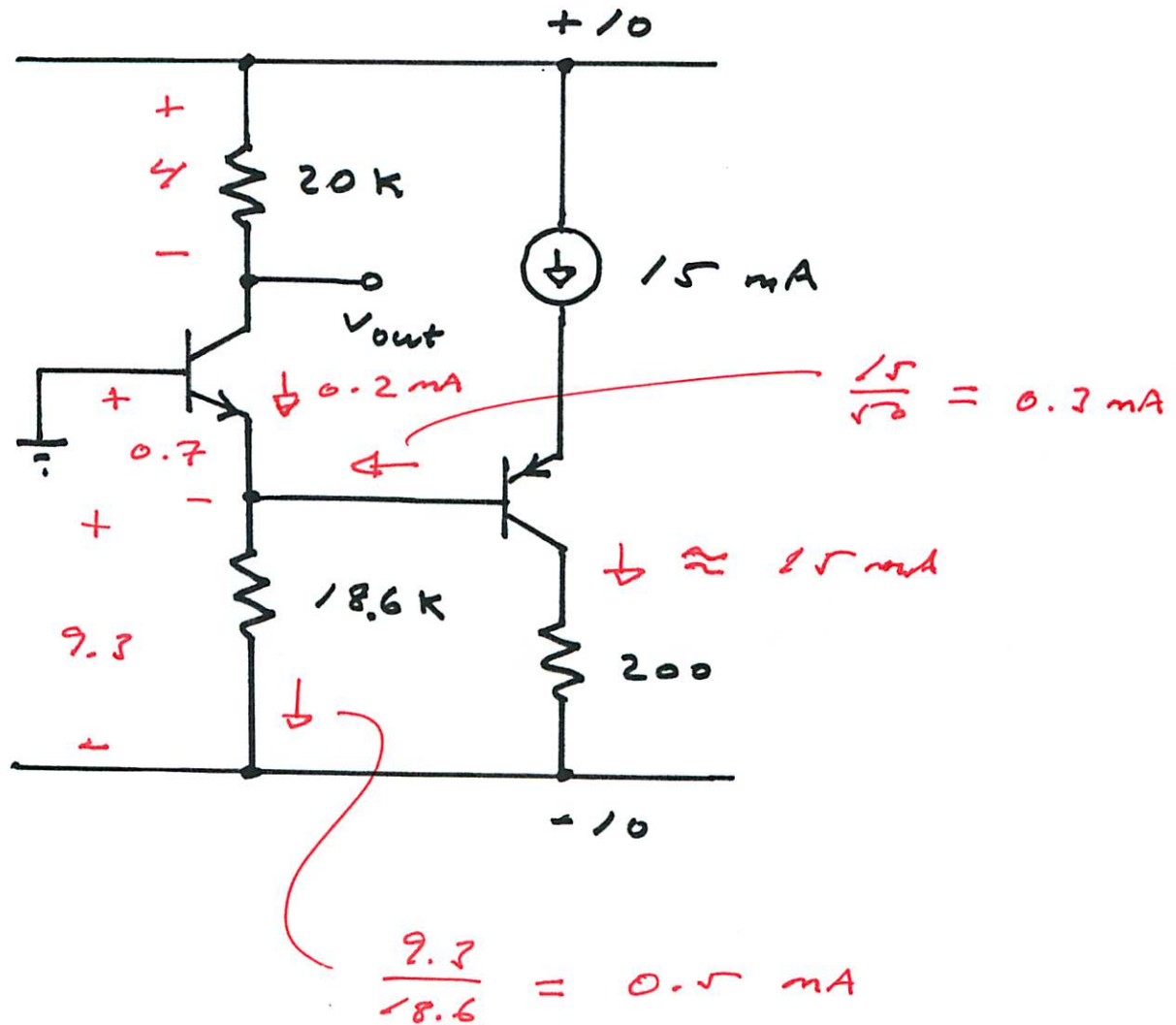
$$\text{so } v_{ds} = 4 \text{ V}$$

$$R_1 = \frac{4 \text{ V}}{4 \text{ mA}} = 1 \text{ k}$$

$$V_S = 7 \text{ V} \rightarrow R_2 = 100 \text{ k}$$

Problem 5

The BJTs have $\beta_F = 50$. Determine v_{out} .



$$v_{out} = 10 - 4 = 6 \text{ V}$$